

ABSTRACT
TANTALUM SPUTTERING TARGET AND METHOD FOR
MANUFACTURING SAME

5 Provided is a tantalum sputtering target having a (200)-plane orientation ratio of 70% or less and a (222)-plane orientation ratio of 10% or more at the sputtering surface of the tantalum sputtering target. The sputter rate can be increased by controlling the crystalline orientation of the target, and thereby a film having an intended thickness can be formed in a short time to improve the throughput.

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Fig. 1